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ABSTRACT OF THE DISCLOSURE

A mask blank has a plurality of pattern formation regions in which mask circuit patterns are to be formed, and a supporting region in which any mask circuit pattern is not to be formed. The supporting region is provided for holding the plurality of pattern formation regions while separating the plurality of pattern formation regions from each other. The supporting region has first and second alignment marks. Exposure of a mask made from the mask blank for forming mask circuit patterns thereon is performed on the basis of the first alignment marks, and exposure of a substrate for forming circuit patterns thereon is performed on the basis of the second alignment marks. With this configuration, a mask used for charged particle beam reduction-and-division transfer exposure can be highly accurately produced at a low cost, and exposure of a substrate can be highly accurately performed by using the mask.